



DMT3006LFVQ

## **Product Summary**

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> Max     | I <sub>D</sub> Max<br>T <sub>C</sub> = +25°C |  |  |
|-------------------|-----------------------------|--|--|--|
| 30V               | $7m\Omega @ V_{GS} = 10V$   | 60A  |  |  |
| 300               | $11m\Omega @ V_{GS} = 4.5V$ | OOA  |  |  |

## Description

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$ , yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- Power Management Functions
- Analog Switch

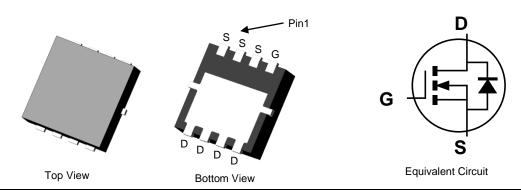
## 30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UX)

#### Features

- Low R<sub>DS(ON)</sub> Ensures On-State Losses are Minimized
- 100% Unclamped Inductive Switching (Test in Production) Ensures More Reliable and Robust End Application
- Small Form Factor Thermally Efficient Package Enables Higher
  Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.03 grams (Approximate)



## Ordering Information (Note 5)

|                | -                       |                   |
|----------------|-------------------------|-------------------|
| Part Number    | Case                    | Packaging         |
| DMT3006LFVQ-7  | PowerDI3333-8 (Type UX) | 2,000/Tape & Reel |
| DMT3006LFVQ-13 | PowerDI3333-8 (Type UX) | 3,000/Tape & Reel |

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



 $\frac{FV6}{YYWW} = \text{Date Code Marking Code}$   $\frac{YYWW}{YY} = \text{Last Two Digits of Year (ex: 18 = 2018)}$ WW = Week Code (01 to 53)

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#### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                     |                 |  | Symbol           | Value    | Unit |
|--|-----------------|--|------------------|----------|------|
| Drain-Source Voltage                               |                 |  | V <sub>DSS</sub> | 30       | V    |
| Gate-Source Voltage                                |                 |  | V <sub>GSS</sub> | ±20      | V    |
| Continuous Drain Current, $V_{GS}$ = 10V (Note 8)  | Steady<br>State | T <sub>C</sub> = +25°C<br>T <sub>C</sub> = +70°C | ID               | 60<br>45 | А    |
| Maximum Body Diode Forward Current (Note 8)        | Is              | 2  | A                |          |      |
| Pulsed Drain Current (380µs Pulse, Duty Cycle = 1% | I <sub>DM</sub> | 90   | A                |          |      |
| Pulsed Drain Body Diode Forward Current (380µs P   | I <sub>SM</sub> | 90   | A                |          |      |
| Avalanche Current (L = 0.1mH) (Note 9)             | I <sub>AS</sub> | 24   | A                |          |      |
| Avalanche Energy (L = 0.1mH) (Note 9)              |                 |  | E <sub>AS</sub>  | 29       | mJ   |

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic  |                  | Symbol                | Value       | Unit |
|---|------------------|-----------------------|-------------|------|
| Total Power Dissipation (Note 6)                              |                  | PD                    | 1.0         | W    |
| Thermal Resistance, Junction to Ambient (Note 6)              | Steady State     | $R_{	extsf{	heta}JA}$ | 130         | °C/W |
| Total Power Dissipation (Note 7)                              |                  | PD                    | 2.0         | W    |
| Thermal Resistance, Junction to Ambient (Note 7) Steady State |                  | $R_{\theta JA}$       | 63          | °C/W |
| Thermal Resistance, Junction to Case (Note 8)                 | R <sub>0JC</sub> | 2.9                   | C/VV        |      |
| Operating and Storage Temperature Range                       |                  | TJ, TSTG              | -55 to +150 | °C   |

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   | Symbol                   | Min | Тур   | Мах  | Unit  | Test Condition   |  |
|--|--------------------------|-----|-------|------|-------|--|--|
| OFF CHARACTERISTICS (Note 10)                          |                          |     |       |      |       |  |  |
| Drain-Source Breakdown Voltage                         | <b>BV</b> <sub>DSS</sub> | 30  | -     | —    | V     | $V_{GS} = 0V, I_D = 250 \mu A$   |  |
| Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C | IDSS                     |     | _     | 1    | μA    | $V_{DS} = 24V, V_{GS} = 0V$  |  |
| Gate-Source Leakage                                    | I <sub>GSS</sub>         | _   | —     | ±100 | nA    | V <sub>GS</sub> = +20V, V <sub>DS</sub> = 0V<br>V <sub>GS</sub> = -16V, V <sub>DS</sub> = 0V |  |
| ON CHARACTERISTICS (Note 10)                           |                          |     | •     |      |       | • • •  |  |
| Gate Threshold Voltage                                 | V <sub>GS(TH)</sub>      | 1.0 | —     | 3.0  | V     | $V_{DS} = V_{GS}$ , $I_D = 250 \mu A$  |  |
| Static Drain-Source On-Resistance                      |                          |     | 5.6   | 7    | mΩ    | $V_{GS} = 10V, I_D = 9.0A$   |  |
| Static Diani-Source On-Resistance                      | R <sub>DS(ON)</sub>      | _   | 8.0   | 11   | 11152 | $V_{GS} = 4.5V, I_D = 8.5A$  |  |
| Diode Forward Voltage                                  | V <sub>SD</sub>          |     | 0.70  | 1.2  | V     | $V_{GS} = 0V, I_S = 1A$  |  |
| DYNAMIC CHARACTERISTICS (Note 11)                      |                          |     |       |      |       |  |  |
| Input Capacitance                                      | Ciss                     |     | 1,155 | —    |       | $V_{DS}$ = 15V, $V_{GS}$ = 0V,<br>f = 1.0MHz   |  |
| Output Capacitance                                     | C <sub>oss</sub>         | _   | 456   | _    | pF    |  |  |
| Reverse Transfer Capacitance                           | C <sub>rss</sub>         |     | 72    | _    |       |  |  |
| Gate Resistance  | Rg                       |     | 1.6   | —    | Ω     | $V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$   |  |
| Total Gate Charge (V <sub>GS</sub> = 4.5V)             | Qg                       |     | 8.4   | —    |       |  |  |
| Total Gate Charge (V <sub>GS</sub> = 10V)              | Qg                       |     | 16.7  | _    | nC    | V <sub>DD</sub> = 15V, I <sub>D</sub> = 9A   |  |
| Gate-Source Charge                                     | Q <sub>gs</sub>          |     | 2.2   | —    | nc    |  |  |
| Gate-Drain Charge                                      | Q <sub>gd</sub>          | _   | 3.5   | _    |       |  |  |
| Turn-On Delay Time                                     | t <sub>D(ON)</sub>       | _   | 3.5   | _    |       | V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V,  |  |
| Turn-On Rise Time                                      | t <sub>R</sub>           | _   | 5.5   | _    |       |  |  |
| Turn-Off Delay Time                                    | t <sub>D(OFF)</sub>      | _   | 13.5  | _    | ns    | $R_G = 3\Omega, I_D = 9A$  |  |
| Turn-Off Fall Time                                     | t <sub>F</sub>           | -   | 4.6   |      |       |  |  |
| Reverse Recovery Time                                  | t <sub>RR</sub>          |     | 19.3  | _    | ns    |  |  |
| Reverse Recovery Charge                                | Q <sub>RR</sub>          | _   | 8.6   | _    | nC    | I <sub>F</sub> = 1.5A, di/dt = 100A/μs   |  |

Notes: 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

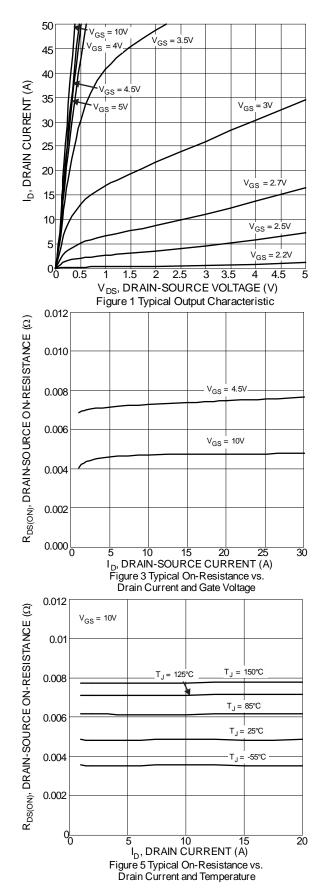
8. Thermal resistance from junction to soldering point (on the exposed drain pad).

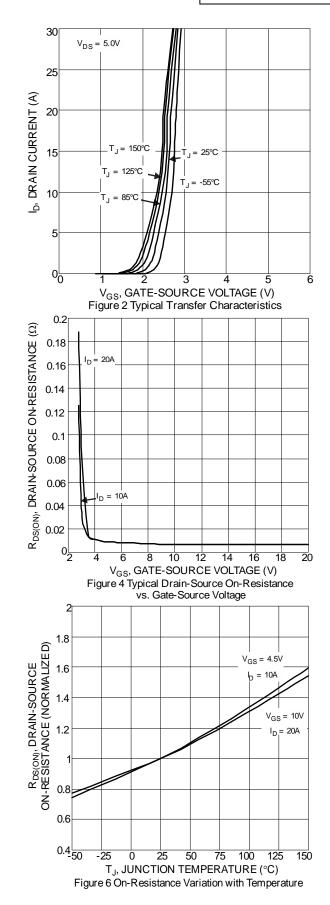
9. IAS and EAS ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ .

10. Short duration pulse test used to minimize self-heating effect.

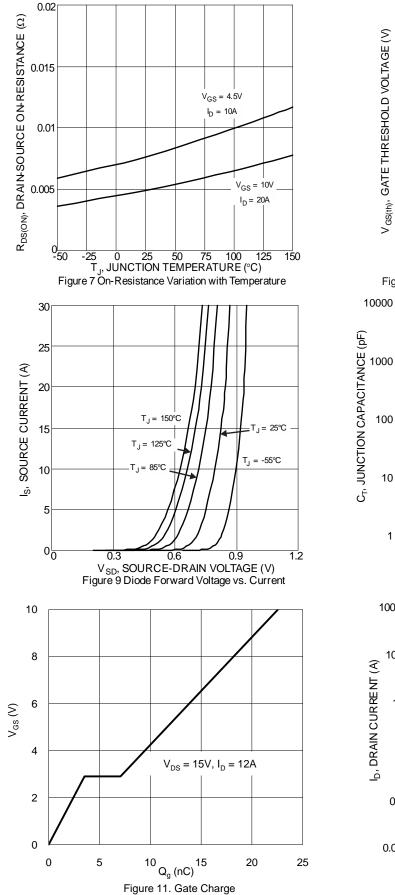
11. Guaranteed by design. Not subject to product testing.

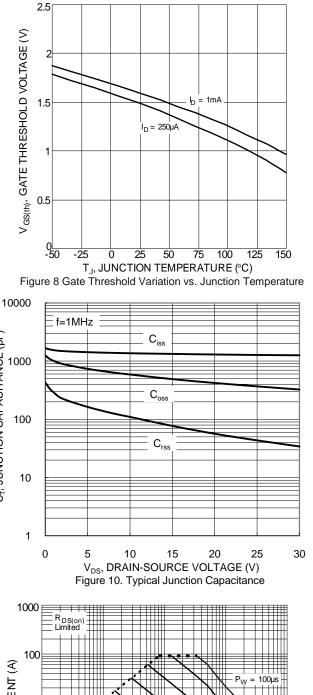


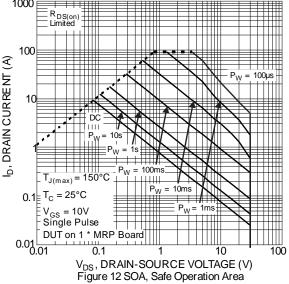




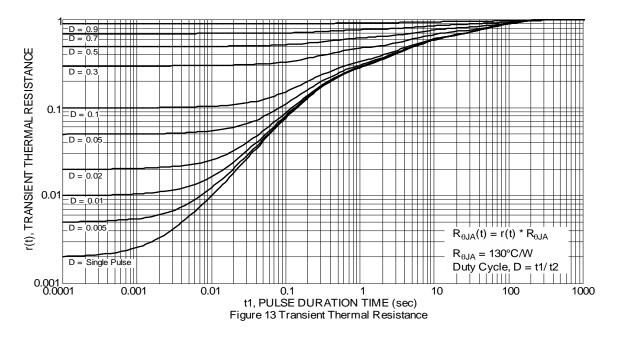










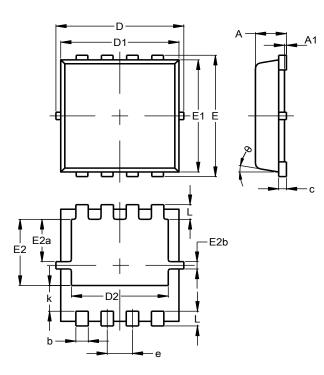




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (Type UX)

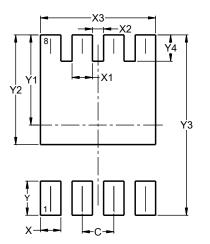


|     | PowerDI3333-8<br>(Type UX) |              |      |  |  |  |
|-----|----------------------------|--------------|------|--|--|--|
| Dim | Min                        | Min Max Ty   |      |  |  |  |
| Α   | 0.75                       | 0.85         | 0.80 |  |  |  |
| A1  | 0.00                       | 0.05         |      |  |  |  |
| b   | 0.25                       | 0.40         | 0.32 |  |  |  |
| С   | 0.10                       | 0.25         | 0.15 |  |  |  |
| D   | 3.20                       | 3.40         | 3.30 |  |  |  |
| D1  | 2.95                       | 2.95 3.15 3. |      |  |  |  |
| D2  | 2.30                       | 2.70         | 2.50 |  |  |  |
| ш   | 3.20                       | 3.40         | 3.30 |  |  |  |
| E1  | 2.95                       | 3.15         | 3.05 |  |  |  |
| E2  | 1.60                       | 2.00         | 1.80 |  |  |  |
| E2a | 0.95                       | 1.35         | 1.15 |  |  |  |
| E2b | 0.10                       | 0.30         | 0.20 |  |  |  |
| е   | 0.65 BSC                   |              |      |  |  |  |
| k   | 0.50                       | 0.90         | 0.70 |  |  |  |
| L   | 0.30                       | 0.50         | 0.40 |  |  |  |
| θ   | 0°                         | 12°          | 10°  |  |  |  |
| All | All Dimensions in mm       |              |      |  |  |  |

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (Type UX)



| Dimensions | Value (in mm) |
|------------|---------------|
| С          | 0.650         |
| Х          | 0.420         |
| X1         | 0.420         |
| X2         | 0.230         |
| X3         | 2.370         |
| Y          | 0.700         |
| Y1         | 1.850         |
| Y2         | 2.250         |
| Y3         | 3.700         |
| Y4         | 0.540         |



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